

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO263 (D2PAK) surface mountable plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$)

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High turn-on current rise $dI_T/dt = 200\text{ A/}\mu\text{s}$
- High noise immunity $dV_D/dt = 1000\text{ V/}\mu\text{s}$ up to 150 °C
- High thermal cycling performance
- High voltage capability

3. Applications

- Ignition circuits
- Protection circuits e.g. SMPS inrush current
- Motor control circuits and starters
- Voltage regulation
- Solid state relays
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)

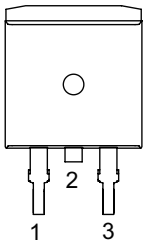
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
V_{DRM}	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 132\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3		50			A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5		500			A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$		550			A
T_j	junction temperature			-40 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7		5	-	35	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9		-	-	60	mA
V_T	on-state voltage	$I_T = 100\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10		-	-	1.70	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		1000	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		 sym037
2	A	anode		
3	K	cathode		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN50B-800TNR	TO263	TYN50B-800TNRJ	Reel	800	TO263d	17-Mar-2023

7. Marking

Table 4. Marking codes

Type number	Marking codes
TYN50B-800TNR	TYN50B 800TNR

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
V_{RRM}	repetitive peak reverse voltage			800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 132\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		50	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5		500	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$		550	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse		1250	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$		200	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current	$t_p = 20\text{ }\mu\text{s}$		5	A
V_{GM}	peak gate voltage	$t_p = 20\text{ }\mu\text{s}$		5	V
P_{GM}	peak gate power	$T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ }\mu\text{s}$		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period		0.5	W
T_{stg}	storage temperature			-40 to 150	$^{\circ}\text{C}$
T_j	junction temperature			-40 to 150	$^{\circ}\text{C}$

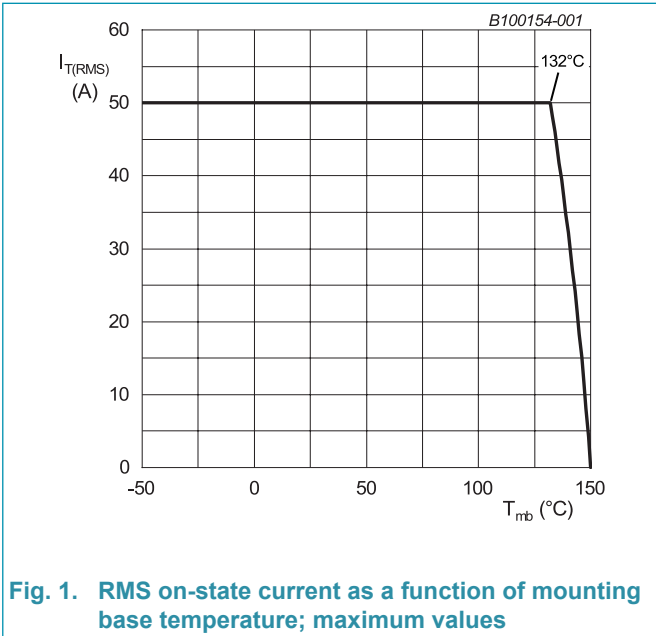


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

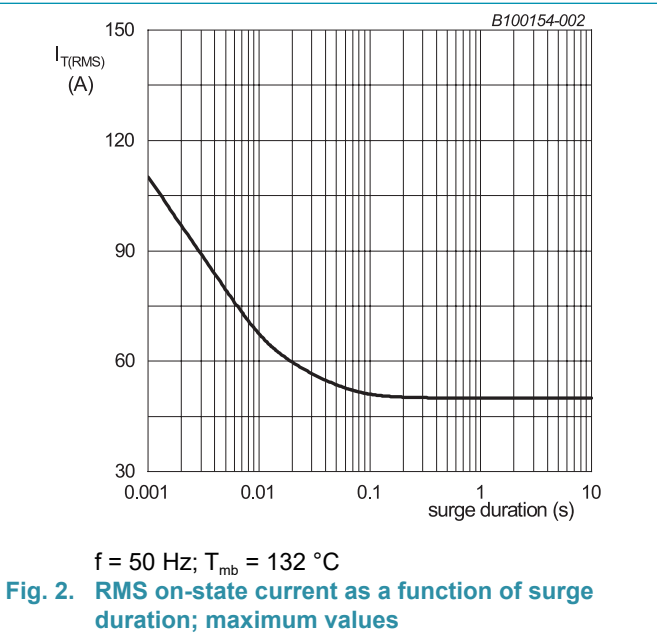


Fig. 2. RMS on-state current as a function of surge duration; maximum values

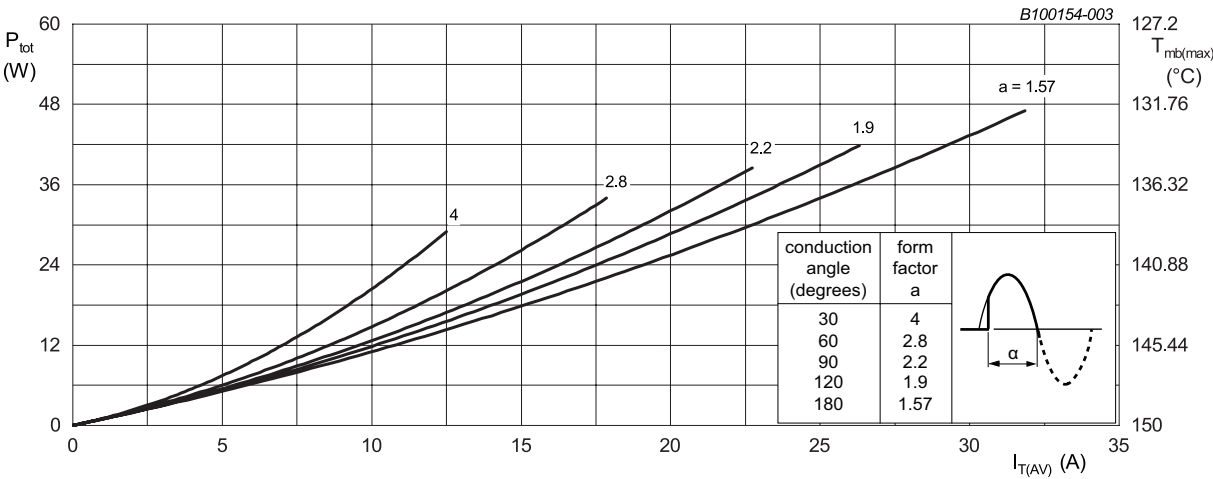
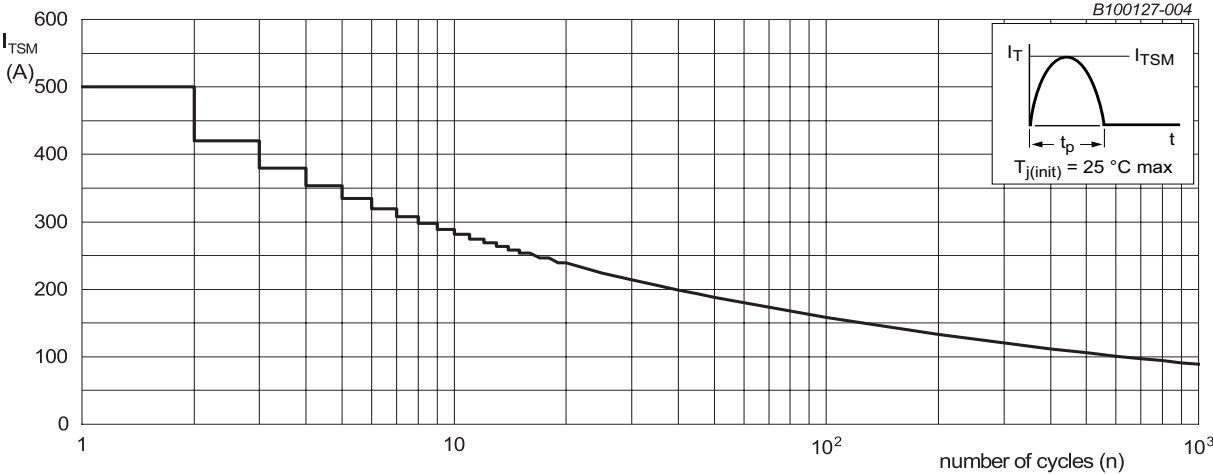
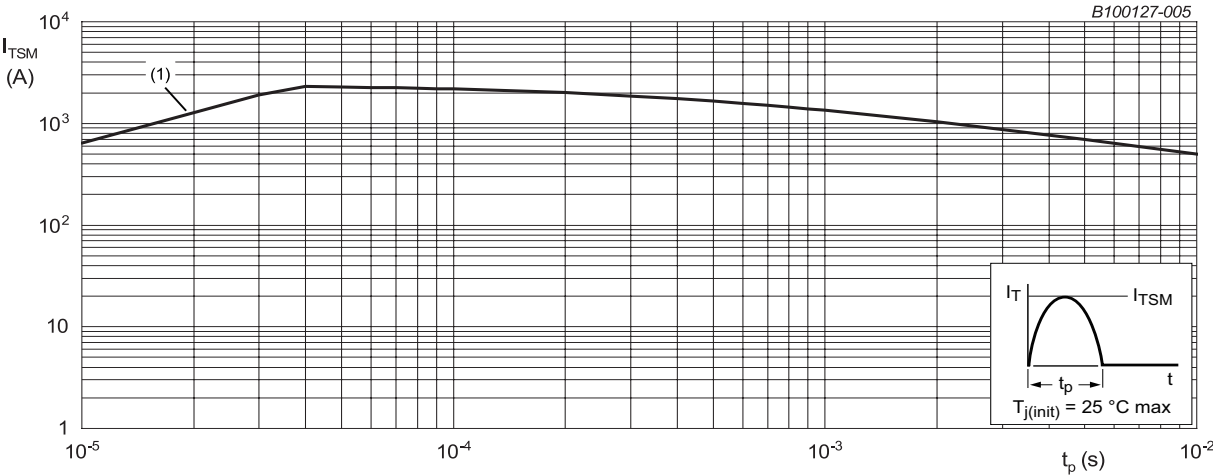


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



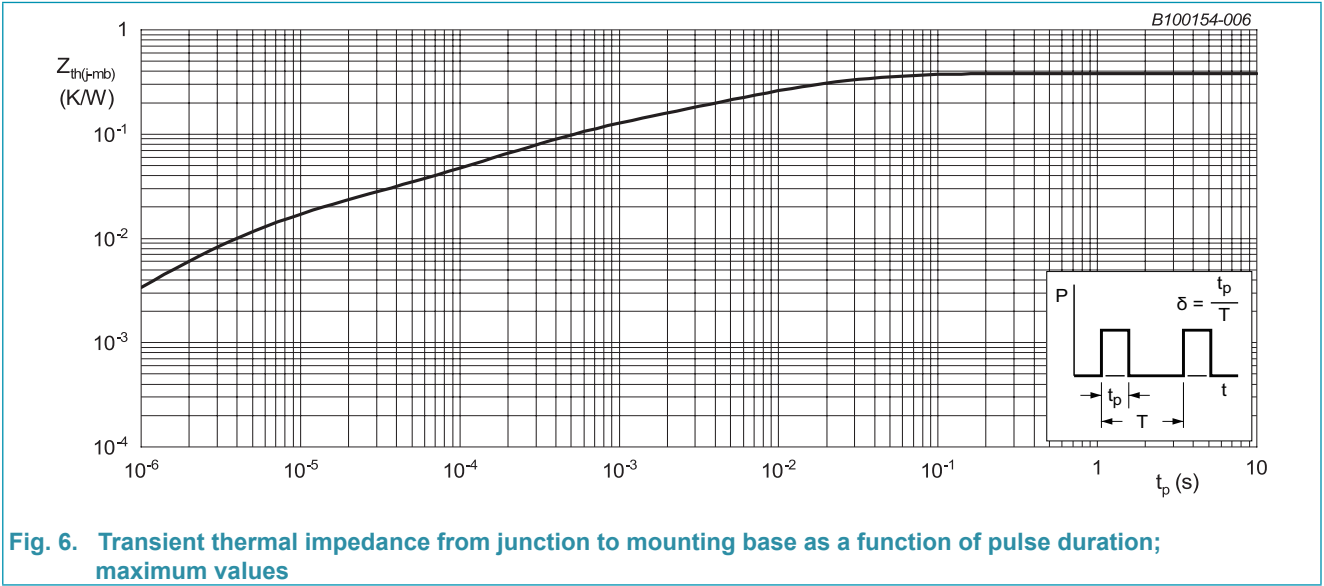
$t_p \leq 10\text{ ms}$
(1) di_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	0.38	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 7		5	-	35	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T _j = 25 °C; Fig. 8		-	-	80	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	-	60	mA
V _T	on-state voltage	I _T = 100 A; T _j = 25 °C; Fig. 10		-	-	1.70	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11		-	0.7	1.0	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C		0.25	0.40	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C		-	-	10	μA
		V _D = 800 V; T _j = 150 °C		-	-	2	mA
I _R	reverse current	V _D = 800 V; T _j = 25 °C		-	-	10	μA
		V _D = 800 V; T _j = 150 °C		-	-	2	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1000	-	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 80 A; V _D = 800 V; I _G = 0.1 A; dI _G /dt = 0.2 A/μs; T _j = 25 °C		-	2	-	μs
t _q	commutated turn-off time	V _{DM} = 536 V; T _j = 150 °C; I _{TM} = 40 A; V _R = 25 V; (d _{IT} /d _i)M = 30 A/μs; dV _D /dt = 50 V/μs; (V _{DM} = 67% of V _{DRM});		-	70	-	μs

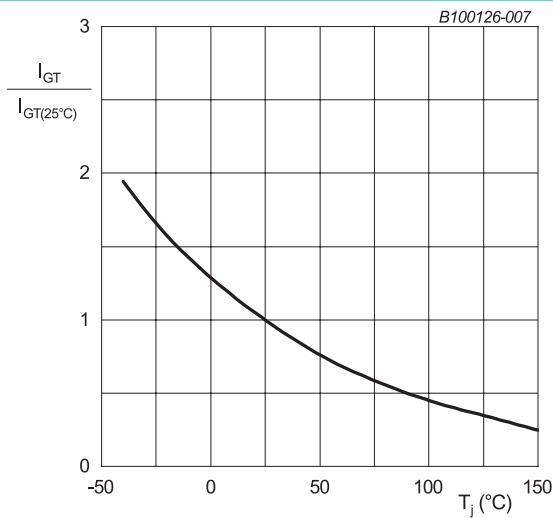


Fig. 7. Normalized gate trigger current as a function of junction temperature

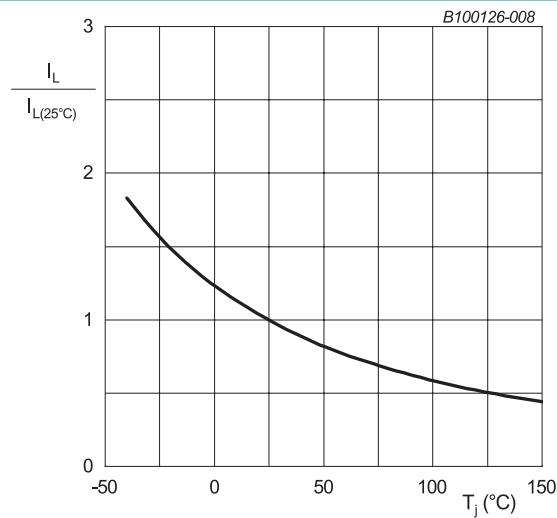


Fig. 8. Normalized latching current as a function of junction temperature

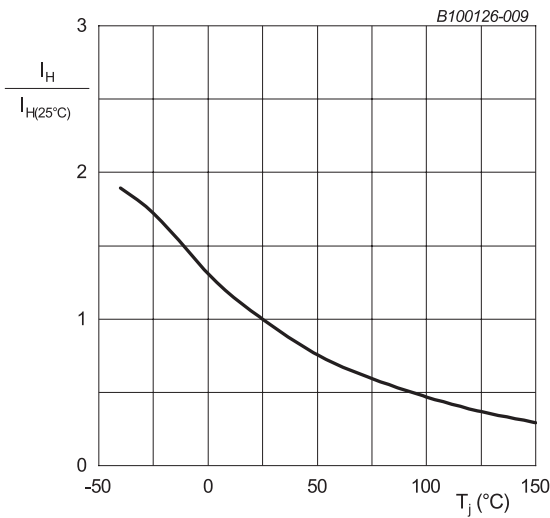
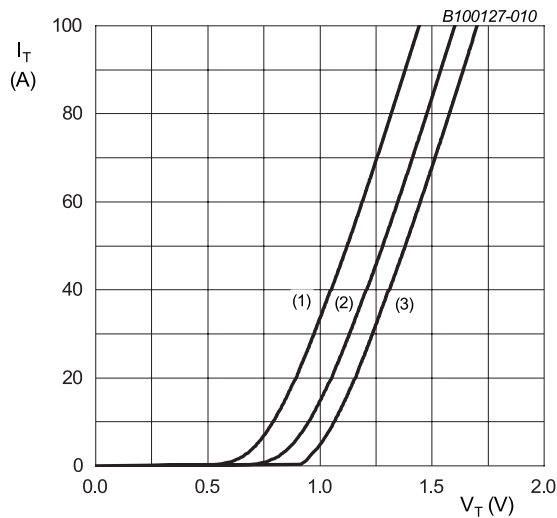


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.932\text{ V}$; $R_s = 0.0069\ \Omega$
(1) $T_j = 150^\circ\text{C}$; typical values
(2) $T_j = 150^\circ\text{C}$; maximum values
(3) $T_j = 25^\circ\text{C}$; maximum values
Fig. 10. On-state current as a function of on-state voltage

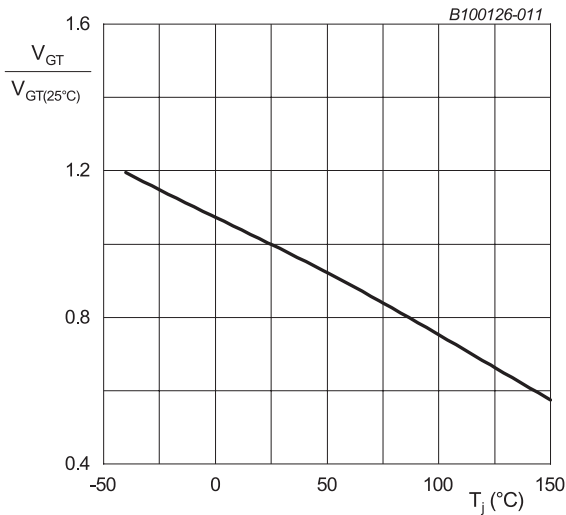
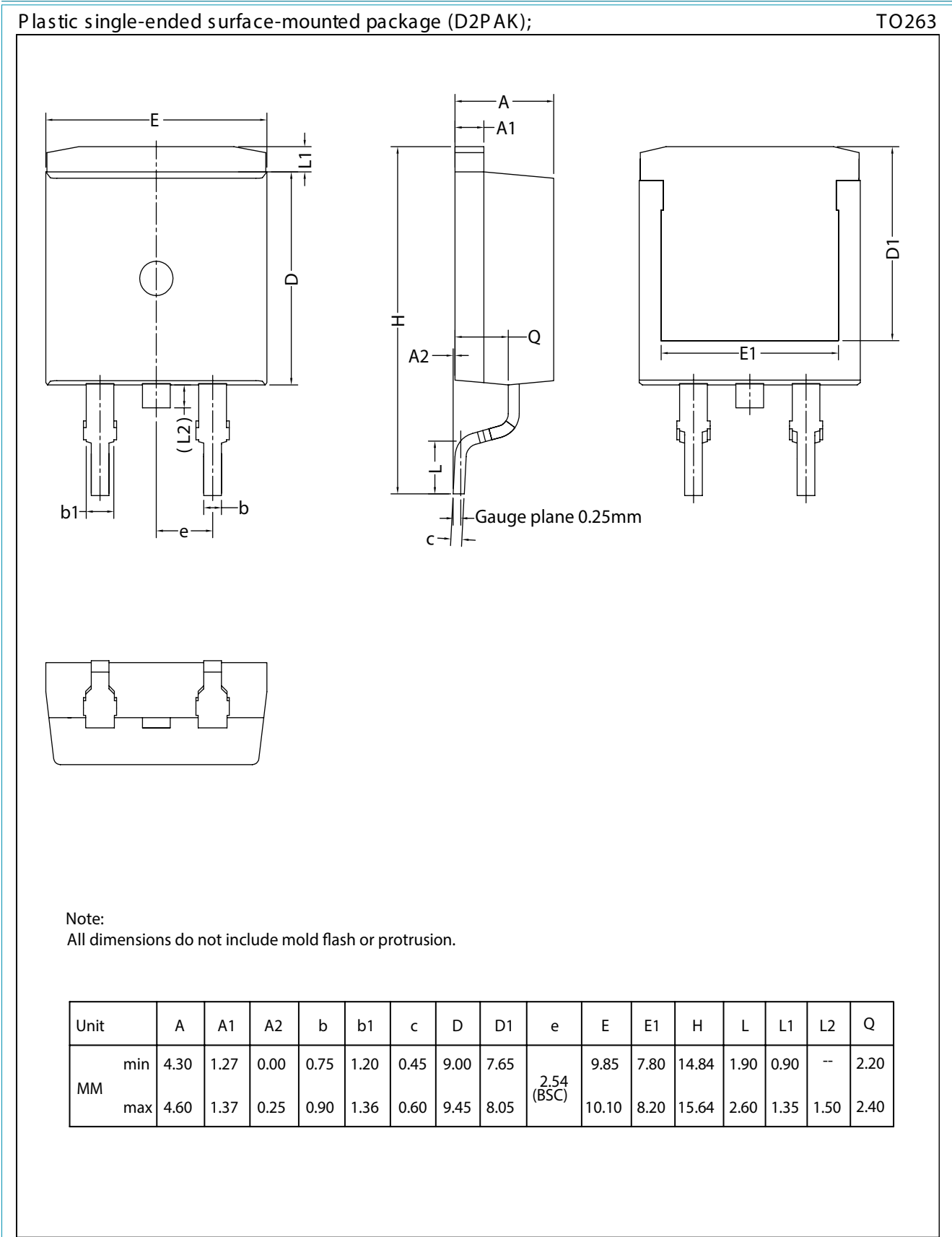


Fig. 10. Normalized gate trigger voltage as a function of junction temperature

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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